

OPD0606

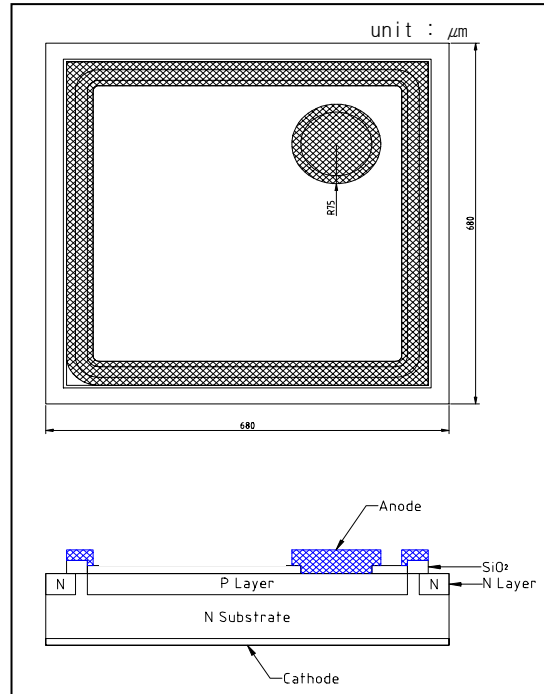
High Speed Sensitivity

Silicon PIN Photo Diode

Common cathode type PIN Photo Diode

1. Structure

- 1.1 Chip Size : 0.68 X 0.68mm
- 1.2 Chip Thickness : 280±20um
- 1.3 Metallization : Top - Al, Bottom - Au
- 1.4 Passivation : Silicon Nitride
- 1.5 Bonding Pad Size
 - Anode(Top) : 150um
 - Cathode(Bottom) : 680um X 680um
- 1.6 Active Area : 0.54mm X 0.54mm



2. Electrical-Optical Characteristics

(Ta=25°C)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Open Circuit Voltage	V _{OP}	0.3	0.32		V	Note(1)
Short Circuit Current	I _{SC}	2	2.6		uA	Note(1)
Spectrum Sensitivity	λ	430~1,100			nm	
Peak Sensing Wavelength	λ _P		780		nm	
Forward Voltage	V _F	0.5		1.3	V	IF=10mA
Dark Current	I _D		5	10	nA	VR=10V
Reverse Breakdown Voltage	BV _R	30			V	IR=10uA

Note(1) : Parallel light of 1,000Lux illumination is applied by a Tungsten lamp of 2856k.

3. Maximum Ratings

(Ta=25°C)

Parameter	Symbol	Rating	Unit
Reverse Breakdown Voltage	BV _R	30	V
Junction Temperature	T _J	150	°C

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